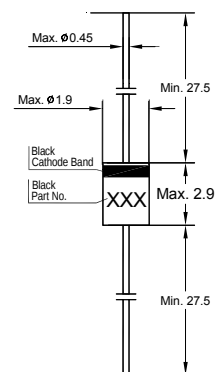


1SS244

SILICON EPITAXIAL PLANAR DIODE

High voltage switching



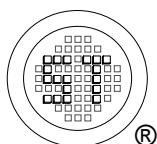
Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	250	V
Reverse Voltage	V_R	220	V
Mean Rectifying Current	I_O	200	mA
Peak Forward Current	I_{FM}	625	mA
Surge Current (1 s)	I_{surge}	1	A
Power Dissipation	P_{tot}	300	mW
Junction Temperature	T_j	175	$^{\circ}\text{C}$
Storage Temperature Range	T_S	- 65 to + 175	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	V_F	1.5	V
Reverse Current at $V_R = 220\text{ V}$	I_R	10	μA
Capacitance between Terminals at $f = 1\text{ MHz}$	C_T	3	pF
Reverse Recovery Time at $I_R = 20\text{ mA}$, $I_F = 20\text{ mA}$, $R_L = 50\text{ }\Omega$	t_{rr}	75	ns



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ISO/TS 16949:2002
Certificate No. 05103

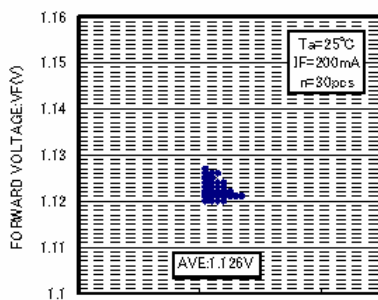
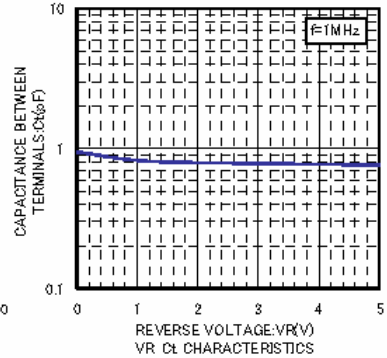
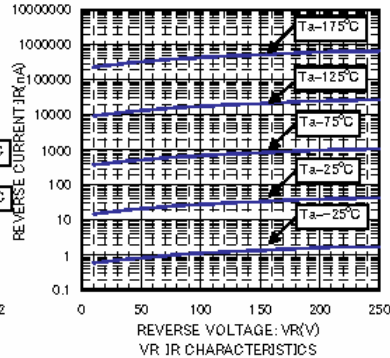
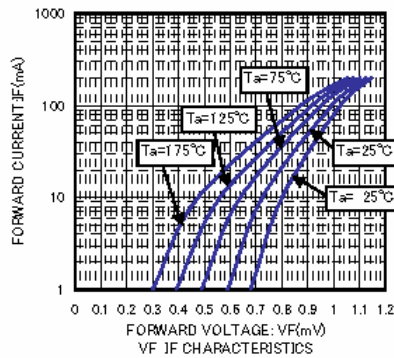


ISO 14001:2004
Certificate No. 7116

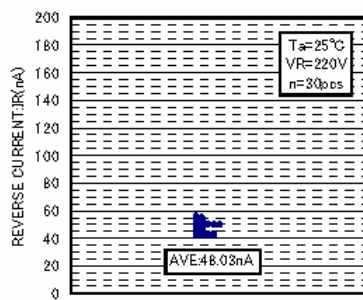


ISO 9001:2000
Certificate No. 0506098

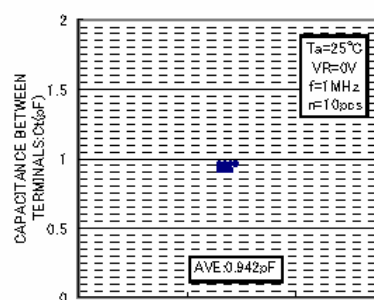
Dated : 23/06/2007



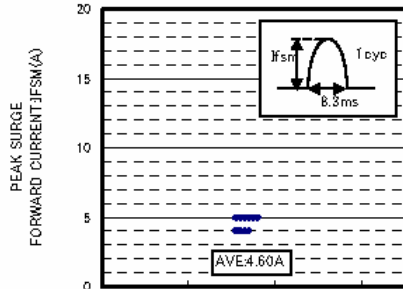
V_F DISPERSION MAP



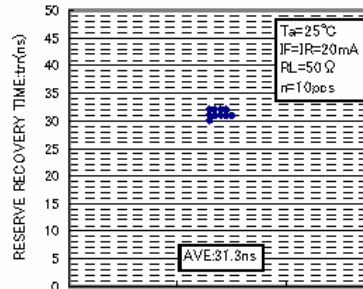
I_R DISPERSION MAP



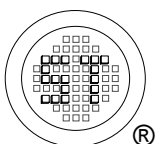
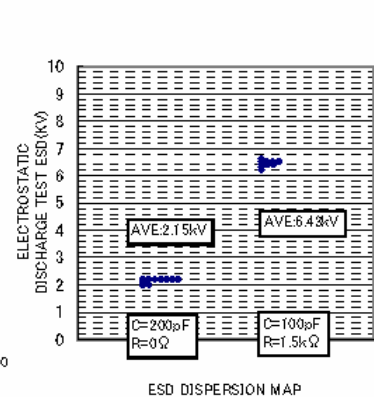
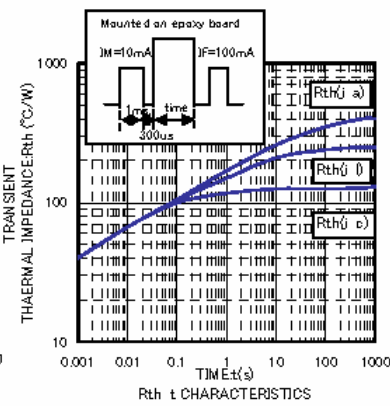
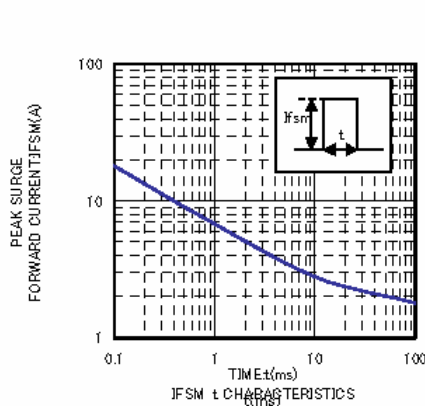
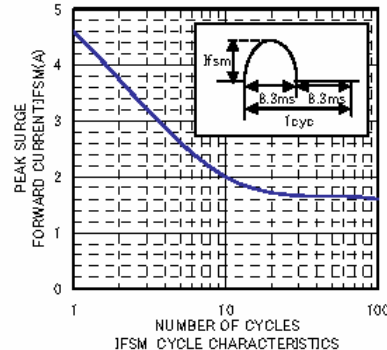
C_T DISPERSION MAP



I_{FSM} DISPERSION MAP



t_{rr} DISPERSION MAP



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Dated : 23/06/2007